Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

- Glass-Passivated Junctions
- Blocking Voltage to 400 Volts
- TO-220 Construction Low Thermal Resistance, High Heat Dissipation and Durability
- Device Marking: Logo, Device Type, e.g., MCR218-2, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to 125°C, Gate Open) MCR218-2 MCR218-4 MCR218-6	VDRM, VRRM	50 200 400	Volts	
On-State RMS Current (180° Conduction Angles; T _C = 70°C)	IT(RMS)	8.0	А	
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 125°C)	ITSM	100	A	
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	26	A ² s	
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 70°C)	PGM	5.0	Watts	
Forward Average Gate Power (t = 8.3 ms, T _C = 70°C)	PG(AV)	0.5	Watts	
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 70°C)	I _{GM}	2.0	А	
Operating Junction Temperature Range	TJ	-40 to +125	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

(1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

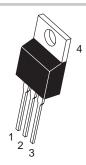


ON Semiconductor

http://onsemi.com

SCRs 8 AMPERES RMS 50 thru 400 VOLTS





TO-220AB CASE 221A STYLE 3

PIN ASSIGNMENT			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

ORDERING INFORMATION

Device	Package	Shipping
MCR218-2	TO220AB	500/Box
MCR218-4	TO220AB	500/Box
MCR218-6	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic		Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise noted.)

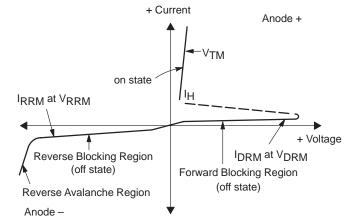
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•	•	
Peak Repetitive Forward or Reverse Blocking Current $(V_{AK} = Rated \ V_{DRM} \ or \ V_{RRM}, \ Gate \ Open)$ $T_{J} = 25^{\circ}C$ $T_{J} = 125^{\circ}C$	I _{DRM} , I _{RRM}	_	=	10 2.0	μA mA
ON CHARACTERISTICS					
Peak Forward On-State Voltage ⁽¹⁾ (I _{TM} = 16 A Peak)	VTM	_	1.5	1.8	Volts
Gate Trigger Current (Continuous dc) (V _D = 12 V, R _L = 100 Ohms)	^I GT	_	10	25	mA
Gate Trigger Voltage (Continuous dc) (V _D = 12 V, R _L = 100 Ohms)	VGT	_	_	1.5	Volts
Gate Non–Trigger Voltage (Rated 12 V, R _L = 100 Ohms, T _J = 125°C)	V _{GD}	0.2	_	_	Volts
Holding Current (V _D = 12 Vdc, Initiating Current = 200 mA, Gate Open)	lн	_	16	30	mA
DYNAMIC CHARACTERISTICS					
Critical Rate-of-Rise of Off-State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)	dv/dt	_	100	_	V/μs

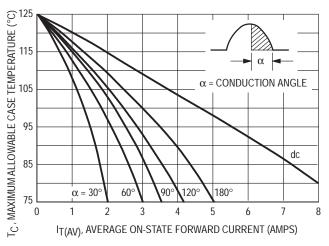
⁽¹⁾ Pulse Test: Pulse Width = 1.0 ms, Duty Cycle ≤ 2%.

15

Voltage Current Characteristic of SCR

Symbol	Parameter
VDRM	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
lΗ	Holding Current





α dc α = Conduction Angle 180° 120° 60° $\alpha = 30^{\circ}$ 1.0 3.0 2.0 4.0 5.0 6.0 7.0 8.0 I_{T(AV)}, AVG. ON-STATE CURRENT (AMPS)

Figure 1. Current Derating

Figure 2. On-State Power Dissipation

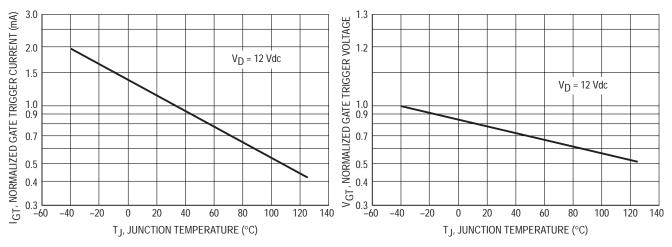


Figure 3. Typical Gate Trigger Current versus Temperature

Figure 4. Typical Gate Trigger Voltage versus Temperature

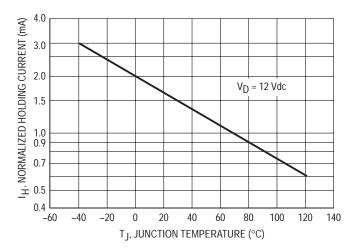
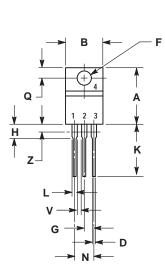
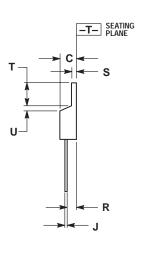


Figure 5. Typical Holding Current versus Temperature

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE Z





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 3: PIN 1. CATHODE 2. ANODE

 - 3. GATE 4. ANODE

Notes



ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada **Fax**: 303–675–2176 or 800–344–3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

German Phone: (+1) 303-308-7140 (M-F 1:00pm to 5:00pm Munich Time)

Email: ONlit-german@hibbertco.com

French Phone: (+1) 303–308–7141 (M–F 1:00pm to 5:00pm Toulouse Time)

Email: ONlit-french@hibbertco.com

English Phone: (+1) 303–308–7142 (M–F 12:00pm to 5:00pm UK Time)

Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

 ${\rm *Available\ from\ Germany,\ France,\ Italy,\ England,\ Ireland}$

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)

Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)

Toll Free from Hong Kong & Singapore:

001-800-4422-3781 Email: ONlit-asia@hibbertco.com

Linan. Ornic-asia @ Hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

Phone: 81–3–5740–2745 **Email**: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.